MC74HC541A

Octal 3-State Noninverting Buffer/Line Driver/Line Receiver

High−Performance Silicon−Gate CMOS

The MC74HC541A is identical in pinout to the LS541. The device inputs are compatible with Standard CMOS outputs. External pull−up resistors make them compatible with LSTTL outputs.

The HC541A is an octal noninverting buffer/line driver/line receiver designed to be used with 3−state memory address drivers, clock drivers, and other bus−oriented systems. This device features inputs and outputs on opposite sides of the package and two ANDed active−low output enables.

The HC541A is similar in function to the HC540A, which has inverting outputs.

Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With the JEDEC Standard No. 7 A Requirements
- Chip Complexity: 134 FETs or 33.5 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable
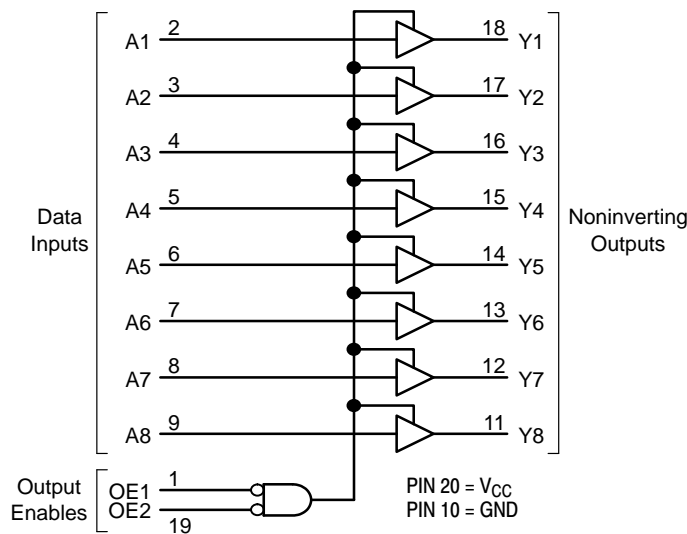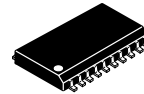- These Devices are Pb−Free and are RoHS Compliant
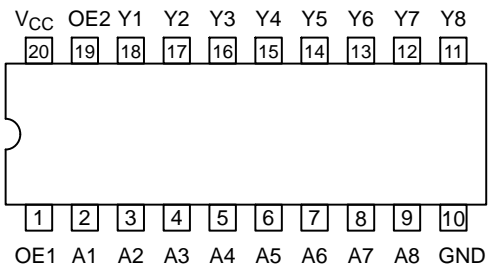

Figure 1. Logic Diagram

PIN 20 = V_{CC}
PIN 10 = GND

ON Semiconductor®

http://onsemi.com

SOIC−20	TSSOP−20
DW SUFFIX	DT SUFFIX
CASE 751D	CASE 948E

PIN ASSIGNMENT

MARKING DIAGRAMS
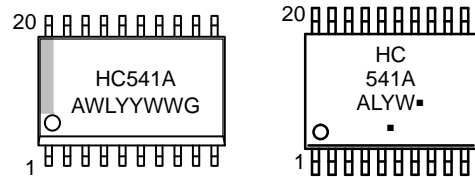
SOIC−20	TSSOP−20

A	= Assembly Location
WL, L	= Wafer Lot
YY, Y	= Year
WW, W	= Work Week
G or ▪	= Pb−Free Package

(Note: Microdot may be in either location)

FUNCTION TABLE

Inputs			Output Y
OE1	OE2	A	
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

X = Don't Care
Z = High Impedance

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

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MC74HC541A

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +7.0	V
V_I	DC Input Voltage		$−0.5 \leq V_I \leq V_{CC} + 0.5$	V
V_O	DC Output Voltage (Note 1)		$−0.5 \leq V_O \leq V_{CC} + 0.5$	V
I_{IK}	DC Input Diode Current		±20	mA
I_{OK}	DC Output Diode Current		±35	mA
I_O	DC Output Sink Current		±35	mA
I_{CC}	DC Supply Current per Supply Pin		±75	mA
I_{GND}	DC Ground Current per Ground Pin		±75	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature under Bias		+150	°C
θ_{JA}	Thermal Resistance	SOIC TSSOP	96 128	°C/W
P_D	Power Dissipation in Still Air at 85°C	SOIC TSSOP	500 450	mW
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen Index: 30% − 35%	UL 94 V−0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 4000 > 300 > 1000	V
$I_{Latchup}$	Latchup Performance	Above V_{CC} and Below GND at 85°C (Note 5)	±300	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. I_O absolute maximum rating must be observed.
2. Tested to EIA/JESD22−A114−A.
3. Tested to EIA/JESD22−A115−A.
4. Tested to JESD22−C101−A.
5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage	(Referenced to GND)	2.0	6.0	V
V_{IN}, V_{OUT}	DC Input Voltage, Output Voltage	(Referenced to GND)	0	V_{CC}	V
T_A	Operating Temperature Range, All Package Types		−55	+125	°C
t_r, t_f	Input Rise/Fall Time (Figure 2)	V_{CC} = 2.0 V V_{CC} = 4.5 V V_{CC} = 6.0 V	0 0 0	1000 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.
6. Unused inputs may not be left open. All inputs must be tied to a high−logic voltage level or a low−logic input voltage level.

MC74HC541A

DC CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Condition	V$_{CC}$ V	Guaranteed Limit –55 to 25°C	≤85°C	≤125°C	Unit
V$_{IH}$	Minimum High–Level Input Voltage	V$_{OUT}$ = 0.1 V |I$_{OUT}$| ≤ 20 µA	2.0 3.0 4.5 6.0	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	V
V$_{IL}$	Maximum Low–Level Input Voltage	V$_{OUT}$ = V$_{CC}$ – 0.1 V |I$_{OUT}$| ≤ 20 µA	2.0 3.0 4.5 6.0	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	V
V$_{OH}$	Minimum High–Level Output Voltage	V$_{IN}$ = V$_{IL}$ |I$_{OUT}$| ≤ 20 µA	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		V$_{IN}$ = V$_{IL}$ |I$_{OUT}$| ≤ 3.6 mA |I$_{OUT}$| ≤ 6.0 mA |I$_{OUT}$| ≤ 7.8 mA	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
V$_{OL}$	Maximum Low–Level Output Voltage	V$_{IN}$ = V$_{IH}$ |I$_{OUT}$| ≤ 20 µA	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		V$_{IN}$ = V$_{IH}$ |I$_{OUT}$| ≤ 3.6 mA |I$_{OUT}$| ≤ 6.0 mA |I$_{OUT}$| ≤ 7.8 mA	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
I$_{IN}$	Maximum Input Leakage Current	V$_{IN}$ = V$_{CC}$ or GND	6.0	±0.1	±1.0	±1.0	µA
I$_{OZ}$	Maximum 3–State Leakage Current	Output in High Impedance State V$_{IN}$ = V$_{IL}$ or V$_{IH}$ V$_{OUT}$ = V$_{CC}$ or GND	6.0	±0.5	±5.0	±10.0	µA
I$_{CC}$	Maximum Quiescent Supply Current (per Package)	V$_{IN}$ = V$_{CC}$ or GND I$_{OUT}$ = 0 µA	6.0	4	40	160	µA

AC CHARACTERISTICS (C$_L$ = 50 pF, Input t$_r$ = t$_f$ = 6 ns)

Symbol	Parameter	V$_{CC}$ V	Guaranteed Limit –55 to 25°C	≤85°C	≤125°C	Unit
t$_{PLH}$, t$_{PHL}$	Maximum Propagation Delay, Input A to Output Y (Figures 2 and 4)	2.0 3.0 4.5 6.0	80 30 18 15	100 40 23 20	120 55 28 25	ns
t$_{PLZ}$, t$_{PHZ}$	Maximum Propagation Delay, Output Enable to Output Y (Figures 3 and 5)	2.0 3.0 4.5 6.0	110 45 25 21	140 60 31 26	165 75 38 31	ns
t$_{PZL}$, t$_{PZH}$	Maximum Propagation Delay, Output Enable to Output Y (Figures 3 and 5)	2.0 3.0 4.5 6.0	110 45 25 21	140 60 31 26	165 75 38 31	ns
t$_{TLH}$, t$_{THL}$	Maximum Output Transition Time, Any Output (Figures 2 and 4)	2.0 3.0 4.5 6.0	60 22 12 10	75 28 15 13	90 34 18 15	ns
C$_{IN}$	Maximum Input Capacitance		10	10	10	pF
C$_{OUT}$	Maximum 3–State Output Capacitance (High Impedance State Output)		15	15	15	pF

		Typical @ 25°C, V$_{CC}$ = 5.0 V, V$_{EE}$ = 0 V	
C$_{PD}$	Power Dissipation Capacitance (Per Buffer) (Note 7)	35	pF

7. Used to determine the no–load dynamic power consumption: P$_D$ = C$_{PD}$ V$_{CC}^2$f + I$_{CC}$ V$_{CC}$.
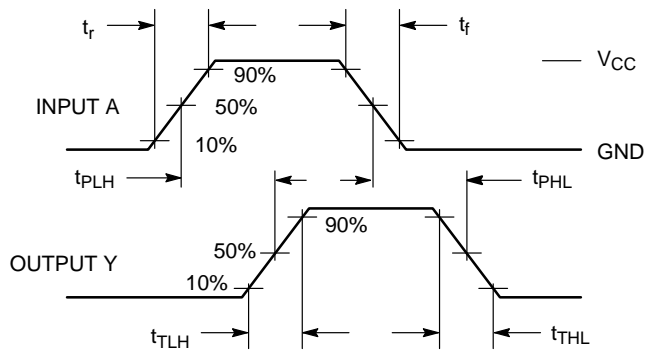
MC74HC541A
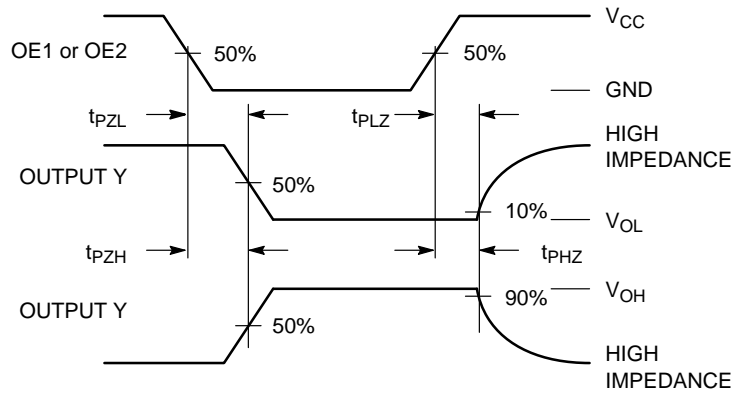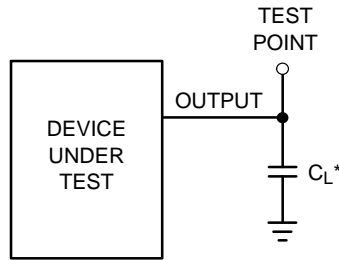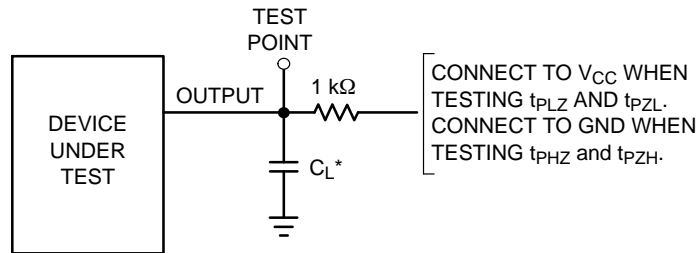

Figure 2. Switching Waveform

Figure 3. Switching Waveform

*Includes all probe and jig capacitance

Figure 4. Test Circuit

CONNECT TO V_{CC} WHEN TESTING t_{PLZ} AND t_{PZL}. CONNECT TO GND WHEN TESTING t_{PHZ} and t_{PZH}.

*Includes all probe and jig capacitance

Figure 5. Test Circuit

MC74HC541A

PIN DESCRIPTIONS

INPUTS

A1, A2, A3, A4, A5, A6, A7, A8 (PINS 2, 3, 4, 5, 6, 7, 8, 9)

Data input pins. Data on these pins appear in non−inverted form on the corresponding Y outputs, when the outputs are enabled.

CONTROLS

OE1, OE2 (PINS 1, 19)

Output enables (active−low). When a low voltage is applied to both of these pins, the outputs are enabled and the device functions as an non−inverting buffer. When a high voltage is applied to either input, the outputs assume the high impedance state.

OUTPUTS

Y1, Y2, Y3, Y4, Y5, Y6, Y7, Y8 (PINS 18, 17, 16, 15, 14, 13, 12, 11)

Device outputs. Depending upon the state of the output enable pins, these outputs are either non−inverting outputs or high−impedance outputs.
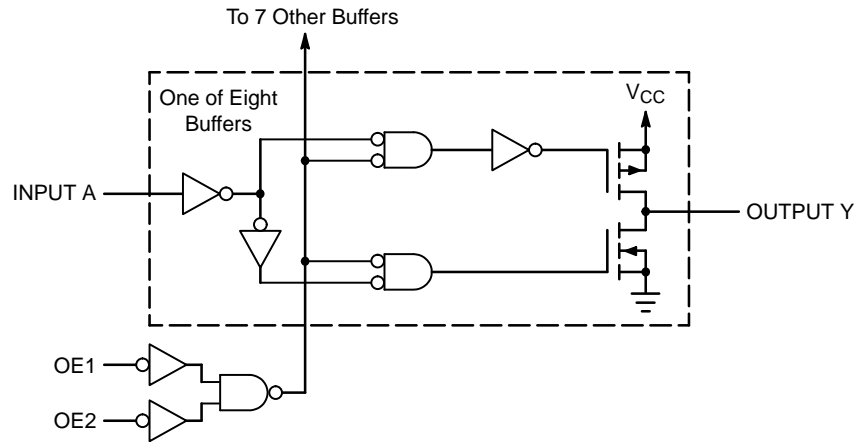
Figure 6. Logic Detail

ORDERING INFORMATION

Device	Package	Shipping†
MC74HC541ADWG	SOIC−20 WIDE (Pb−Free)	38 Units / Rail
MC74HC541ADWR2G	SOIC−20 WIDE (Pb−Free)	1000 Tape & Reel
NLV74HC541ADWR2G*	SOIC−20 WIDE (Pb−Free)	1000 Tape & Reel
MC74HC541ADTG	TSSOP−20 (Pb−Free)	75 Units / Rail
MC74HC541ADTR2G	TSSOP−20 (Pb−Free)	2500 Tape & Reel
NLV74HC541ADTR2G*	TSSOP−20 (Pb−Free)	2500 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable.

SOIC−20 WB
CASE 751D−05
ISSUE H

DATE 22 APR 2015

SCALE 1:1

NOTES:
1. DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS	
	MIN	MAX
A	2.35	2.65
A1	0.10	0.25
b	0.35	0.49
c	0.23	0.32
D	12.65	12.95
E	7.40	7.60
e	1.27 BSC	
H	10.05	10.55
h	0.25	0.75
L	0.50	0.90
θ	0 °	7 °

RECOMMENDED SOLDERING FOOTPRINT*

DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*
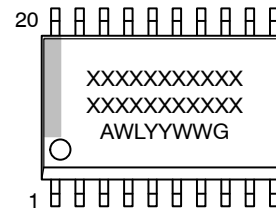
XXXXX = Specific Device Code
A   = Assembly Location
WL   = Wafer Lot
YY   = Year
WW   = Work Week
G   = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98ASB42343B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOIC−20 WB		PAGE 1 OF 1

TSSOP−20 WB
CASE 948E
ISSUE D

DATE 17 FEB 2016

SCALE 2:1

| ⊕ | 0.15 (0.006) | T | U | Ⓢ |

20X K REF

| ⊕ | 0.10 (0.004) | Ⓜ | T | U | Ⓢ | V | Ⓢ |

2X L/2

PIN 1 IDENT

| ⊕ | 0.15 (0.006) | T | U | Ⓢ |

K
K1

J J1

SECTION N−N

0.25 (0.010)

N **N** **M** **F**

DETAIL E

C **D** **G** **H**

| ◺ | 0.100 (0.004) |

−T− SEATING PLANE

−W−

DETAIL E

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	6.40	6.60	0.252	0.260
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

SOLDERING FOOTPRINT

7.06

1

0.65 PITCH

16X 0.36

16X 1.26

DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*

XXXX
XXXX
ALYW▪

A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present.

DOCUMENT NUMBER:	98ASH70169A		
DESCRIPTION:	TSSOP−20 WB		**PAGE 1 OF 1**

PUBLICATION ORDERING INFORMATION

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